

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
-40V	25mΩ @ V _{GS} = -10V	-28A
	45mΩ @ V _{GS} = -4.5V	-21A

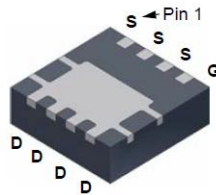
Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

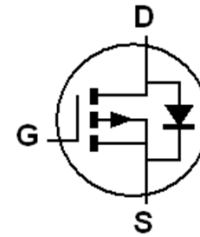
- Motor controls
- Backlighting
- DC-DC converters
- Printer equipment



Top View



Bottom View



Device Symbol

Features and Benefits

- Low R_{DS(ON)} – Minimizes Conduction Losses
- Fast Switching Speed – Minimizes Switching Losses
- 100% Unclamped Inductive Switch (UIS) Test in Production
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **The DMP4026SFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

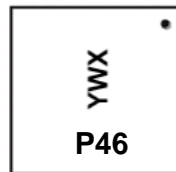
- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.0172 grams (Approximate)

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP4026SFGQ-7	PowerDI3333-8	2,000	Reel
DMP4026SFGQ-13	PowerDI3333-8	3,000	Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, “Green” and Lead-free.
 3. Halogen- and Antimony-free “Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



P46 = Product Type Marking Code
 YWX = Date Code Marking
 Y = Year (ex: 3 = 2023)
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)
 X = Internal Code (ex: U = Monday)

Date Code Key

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	2	3	4	5	6	7	8	9	0	1	2	3
Week	1-26				27-52				53			
Code	A-Z				a-z				z			
Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat					
Code	T	U	V	W	X	Y	Z					

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-40	V
Gate-Source Voltage	V _{GSS}	±20	
Continuous Drain Current (Note 6), V _{GS} = -10V	I _D	T _C = +25°C	-28
		T _C = +70°C	-22
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	-28	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-113	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	-113	
Avalanche Current, L = 0.3mH	I _{AS}	-20	
Avalanche Energy, L = 0.3mH	E _{AS}	65	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	48	°C/W
Total Power Dissipation (Note 6)	P _D	33	W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	3.8	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-40	—	—	V	I _D = -250µA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0	µA	V _{DS} = -40V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.8	—	-1.8	V	I _D = -250µA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance	R _{DS(ON)}	—	15	25	mΩ	V _{GS} = -10V, I _D = -3A
		—	18	45		V _{GS} = -4.5V, I _D = -3A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.0	V	I _S = -1A, V _{GS} = 0V
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	2275	—	pF	V _{DS} = -20V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	215	—		
Reverse Transfer Capacitance	C _{rss}	—	197	—		
Gate Resistance	R _g	—	2.3	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -10V)	Q _g	—	48	—	nC	V _{DS} = -20V, I _D = -3A
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	25	—		
Gate-Source Charge	Q _{gs}	—	4	—		
Gate-Drain Charge	Q _{gd}	—	8	—		
Turn-On Delay Time	t _{D(ON)}	—	4.5	—	ns	V _{DD} = -20V, V _{GS} = -10V I _D = -3A, R _G = 6Ω
Turn-On Rise Time	t _r	—	5.6	—		
Turn-Off Delay Time	t _{D(OFF)}	—	75	—		
Turn-Off Fall Time	t _f	—	26	—		
Body Diode Reverse Recovery Time	t _{RR}	—	18.5	—	ns	I _S = -3A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	9.5	—	nC	I _S = -3A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

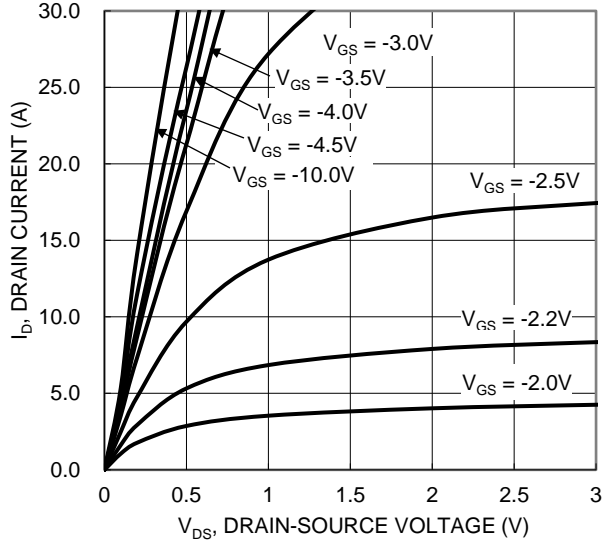


Figure 1. Typical Output Characteristic

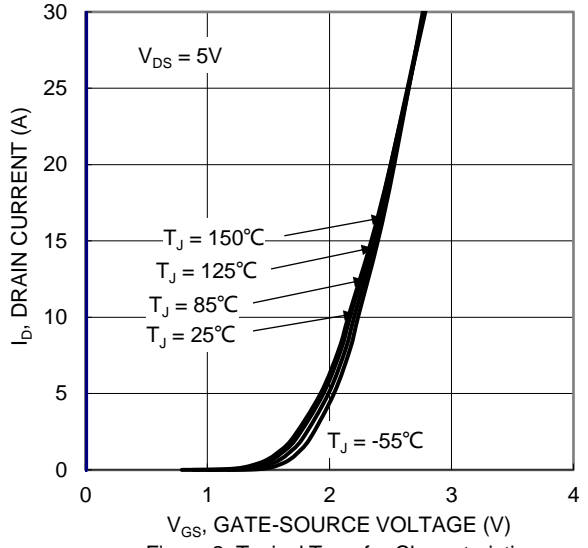


Figure 2. Typical Transfer Characteristic

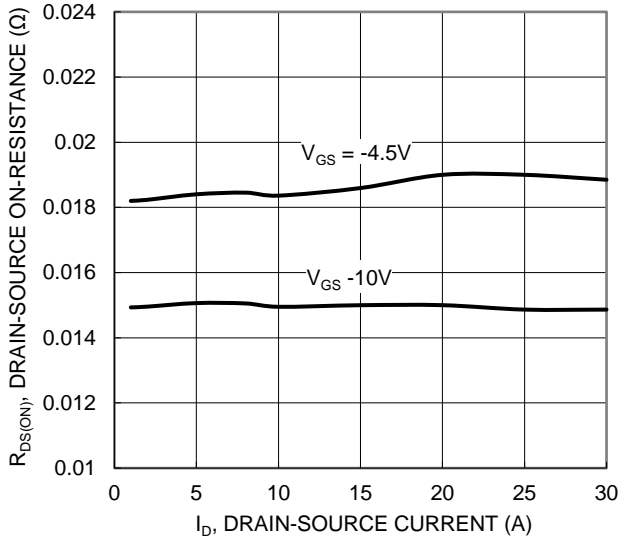


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

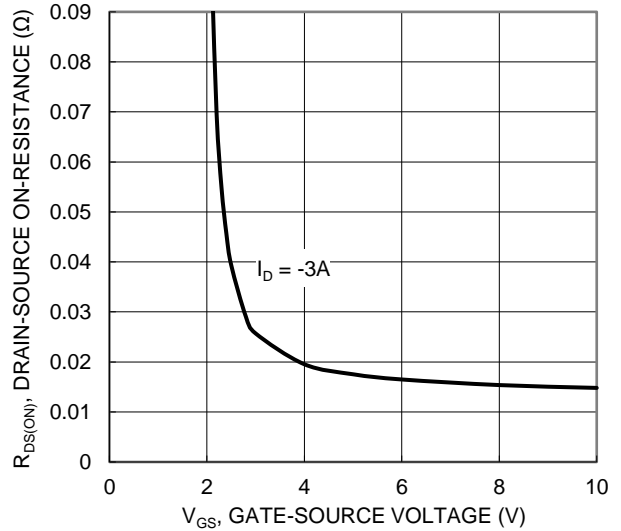


Figure 4. Typical Transfer Characteristic

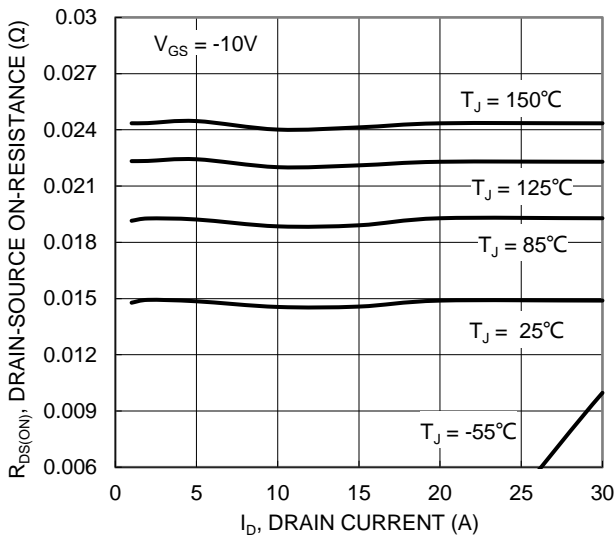


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

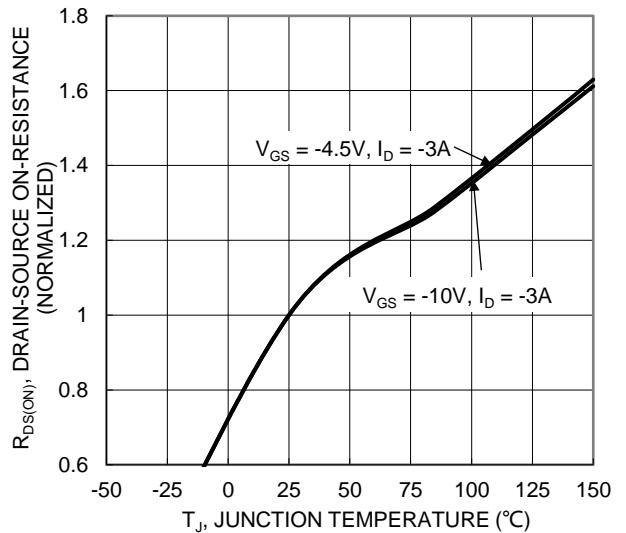


Figure 6. On-Resistance Variation with Junction Temperature

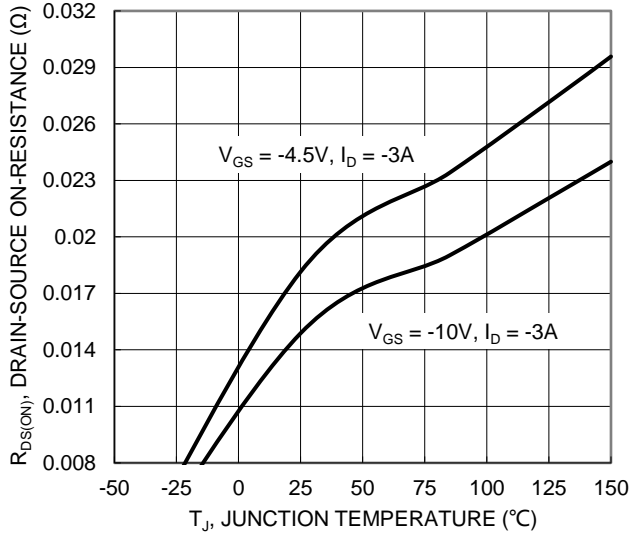


Figure 7. On-Resistance Variation with Junction Temperature

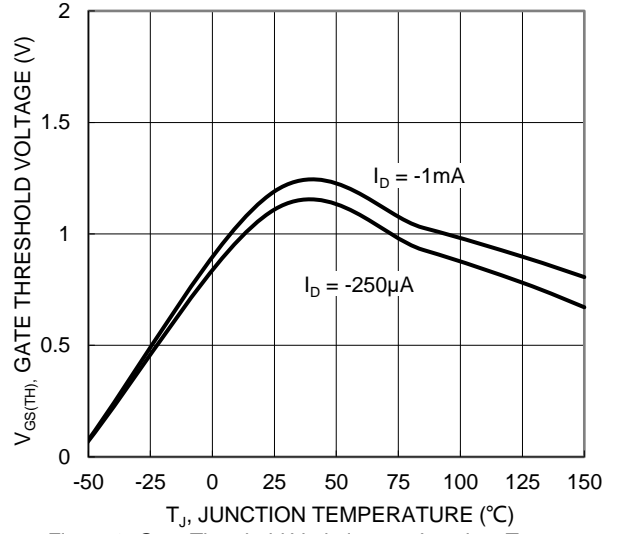


Figure 8. Gate Threshold Variation vs. Junction Temperature

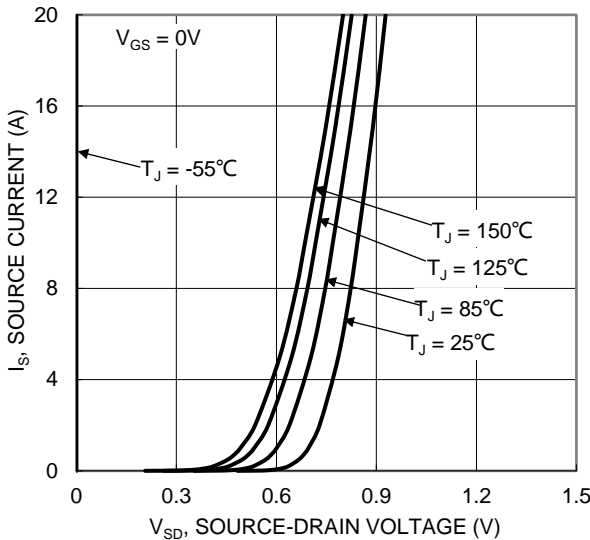


Figure 9. Diode Forward Voltage vs. Current

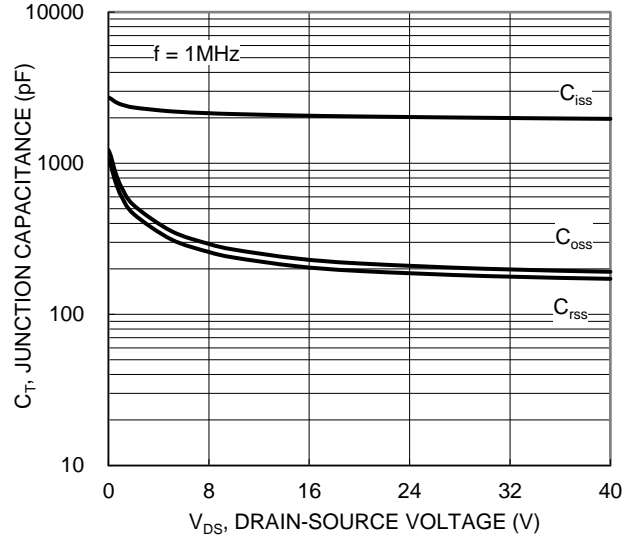


Figure 10. Typical Junction Capacitance

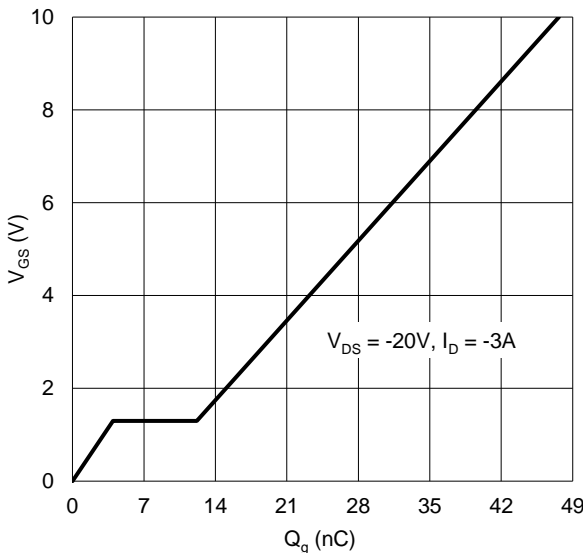


Figure 11. Gate Charge

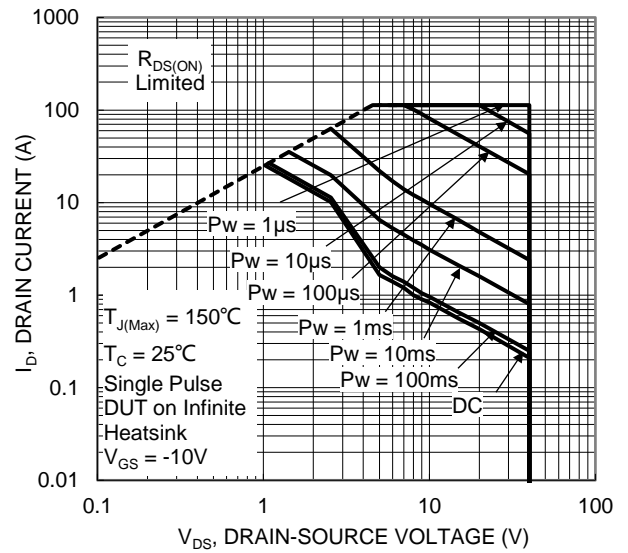


Figure 12. SOA, Safe Operation Area

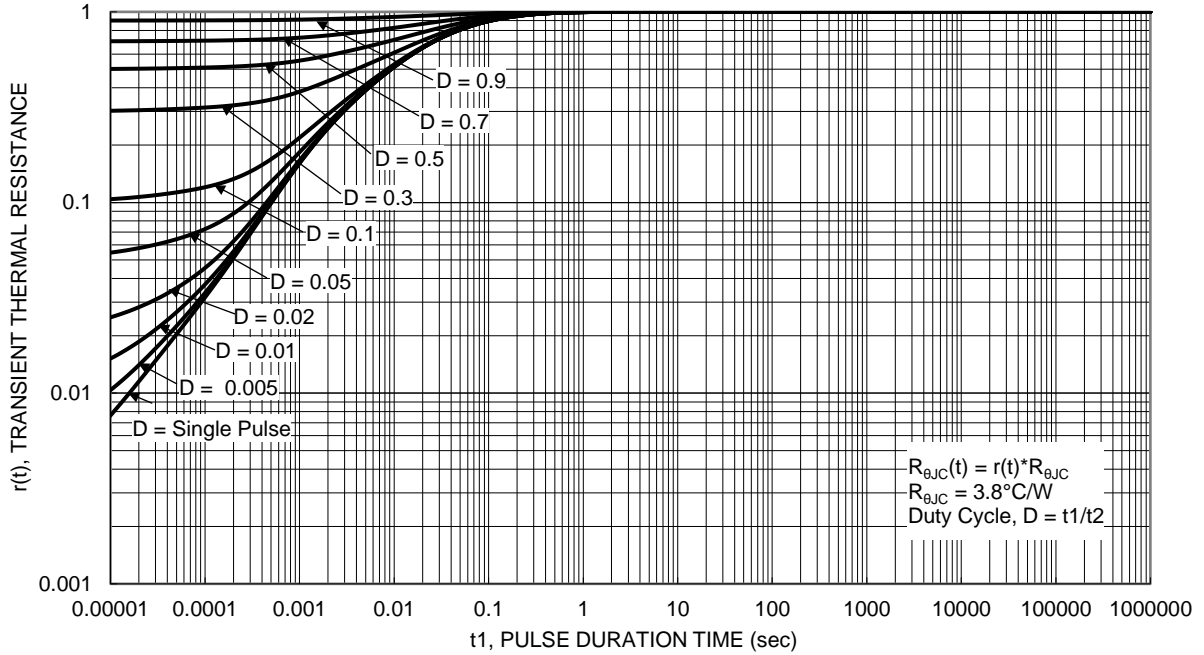
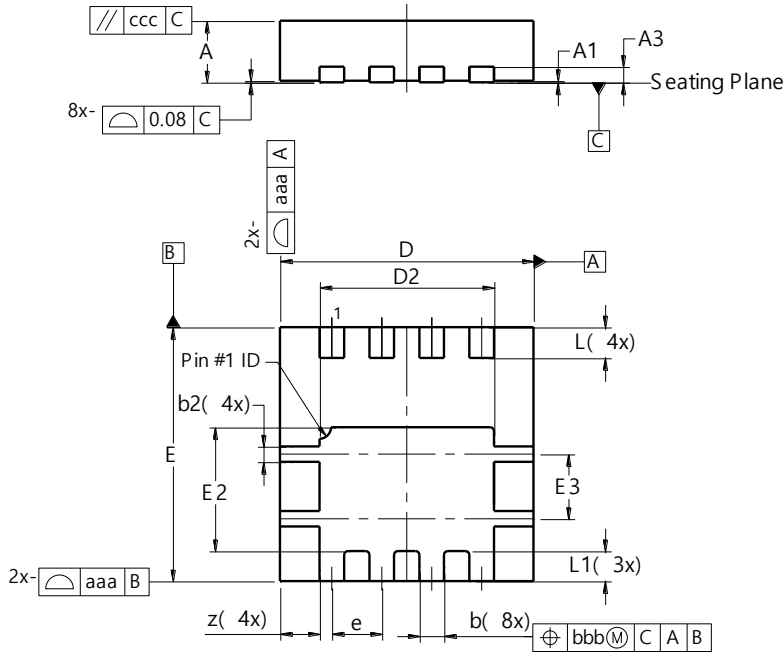


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8

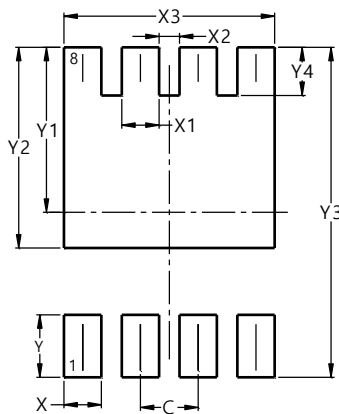


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	-	-	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
e	-	-	0.65
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
aaa	0.25		
bbb	0.10		
ccc	0.10		
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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